

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method for eliminating boron contamination in an annealed wafer, the method comprising, when annealing a silicon wafer having a surface on which a native oxide film has formed ~~and~~ containing boron of environmental origin or from chemical treatment prior to the annealing, ~~has deposited, steps of~~ carrying out temperature heat-up in a mixed gas atmosphere having a ~~mixing-ratio~~ ratio of hydrogen gas to an inert gas of 5% to 100% so as to remove the boron-containing native oxide film, followed by annealing in an inert gas atmosphere.

2. (Currently Amended) The method for eliminating boron contamination in an annealed wafer according to claim 1, wherein a treatment temperature of the temperature heat-up in the mixed gas atmosphere is from 700°C to 1,200°C.

3. (Currently Amended) The method for eliminating boron in an annealed wafer according to claim 1 ~~or 2~~, wherein the temperature heat-up is carried out in the mixed gas atmosphere in which the ~~mixing-ratio~~ ratio of the hydrogen gas to the inert gas is from 10% to 30%.

4. (New) The method for eliminating boron in an annealed wafer according to claim 2, wherein the temperature heat-up is carried out in the mixed gas atmosphere in which the ratio of the hydrogen gas to the inert gas is from 10% to 30%.